

MICRO ELECTRONICS

2SA928
PNP
SILICON
TRANSISTOR

DESCRIPTION

2SA928 is PNP silicon planar transistor dedesigned for audio power amplifier.

TO-92B



ECB

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	30V
Collector-Emitter Voltage	VCEO	30V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	2A
Continuous Power Dissipation	Pd	1W
Operating & Storage Junction Temperature	Tj, Tstg	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS	
Collector-Base Breakdown Voltage	BVCBO	30				IC=100μA IE=0	
Collector-Emitter Breakdown Voltage	BVCEO	30			V	IC=10mA IB=0	
Emitter-Base Breakdown Voltage	BVEBO	5			V	IE=1mA IC=0	
Collector Cutoff Current	ICBO			100	nA	VCB=30V IE=0	
Emitter Cutoff Current	IEBO			100	nA	VEB=5V IC=0	
D.C. Current Gain	HFE	100		320		IC=500mA VCE=2V	
			GROUP -O	100		200	IC=500mA VCE=2V
			GORUP -Y	160		320	IC=500mA VCE=2V
Base-Emitter Voltage	VBE			1.0	V	IC=500mA VCE=2V	
Collector-Emitter Saturation Voltage	VCE(sat)			2.0	V	IC=1.5A IB=0.03A	
Output Capacitance	Cob		48		pF	VCB=10V f=1MHz	
Current Gain Bandwidth Product	fT		120		MHz	IC=500mA VCE=2V	



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